

KSC5042M

High Voltage Switching Dynamic Focus Application

- High Collector-Emitter Breakdown Voltage : BV_{CEO}=900V
- Small C_{ob} =2.8pF (Typ.)
 Wide S.O.A
- High reliability



NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	1500	V
V _{CEO}	Collector-Emitter Voltage	900	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current (DC)	100	mA
I _{CP}	Collector Current (Pulse)	300	mA
P _C	Collector Dissipation (T _C =25°C)	4	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 1 \text{mA}, I_E = 0$	1500			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	900			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	5			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 900V, I_{E} = 0$			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$			10	μΑ
h _{FE}	DC Current Gain	$V_{CE} = 5V, I_{C} = 10mA$	30			
V _{CE (sat)}	Collector-Emitter Saturation Voltage	$I_C = 20$ mA, $I_B = 4$ mA			5	V
V _{BE (sat)}	Base-Emitter Saturation Voltage	$I_C = 20$ mA, $I_B = 4$ mA			2	V
C _{ob}	Output Capacitance	V _{CB} = 100V, f = 1MHz		2.8		pF

Typical Characteristics

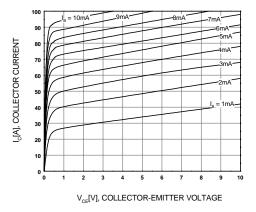


Figure 1. Static Characteristic

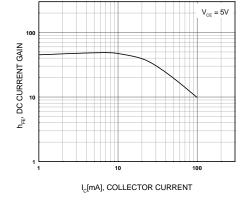


Figure 2. DC current Gain

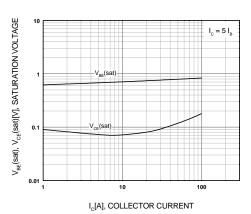


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

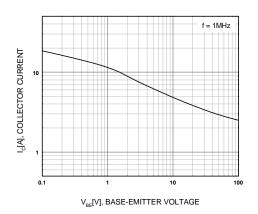


Figure 4. Collector-Base Capacitance

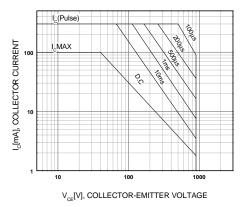


Figure 5. Safe Operating Area

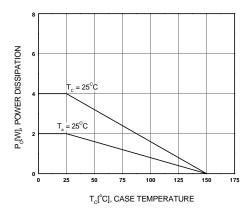
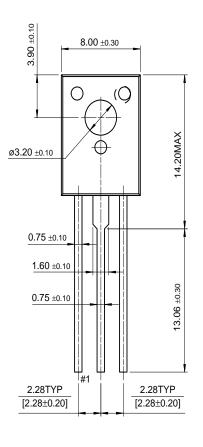


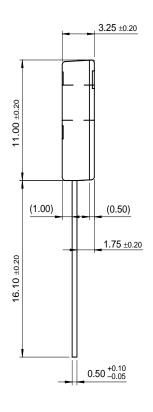
Figure 6. Power Derating

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Package Dimensions

TO-126







Dimensions in Millimeters

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